

INFORMATION DISCLOSURE CITATION <i>(Use several sheets if necessary)</i>		<div style="border: 1px solid black; border-radius: 50%; padding: 5px; display: inline-block;"> APR 12 2006 <small>RECEIVED</small> </div>		4/12/06	
		Docket Number (Optional) F05-420-US		Application Number 10/564,416	
Applicant(s) Masanobu ANDO, et al.				Filing Date January 12, 2006	
Group Art Unit Not Yet Assigned					

U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

U.S. PATENT APPLICATION PUBLICATIONS							
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
SWC		2002/0171092 A1	11/21/2002	GOETZ, et al.			

FOREIGN PATENT DOCUMENTS								
	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO
SWC		EP 1 280 212 A2	01/29/2003	Europe				
SWC		0 662 739 A1	07/12/1995	Europe				
SWC		11-026812	01/29/1999	Japan				ABS ONLY

OTHER DOCUMENTS			(Including Author, Title, Date, Pertinent Pages, Etc.)
SWC		European Search Report dated March 8, 2006	

EXAMINER CRANE	DATE CONSIDERED 6/2006
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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation YES NO
OTHER DOCUMENTS <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>							
SWL		Kneissl, et al. "Continuous-wave operation of ultraviolet InGaN/InAlGaN multiple-quantum-well laser diodes", Applied Physics Letters, AIP, American Institute of Physics, Melville, NY, US, Vol. 82, No. 15, April 14, 2003, Pages 2386-2388, XP012033738.					
SWL		Nakamura, et al. "InGaN/GaN/AlGaIn-based laser diodes with modulation-doped strained-layer superlattices grown on an epitaxially laterally overgrown GaN substrate", Applied Physics Letter, AIP, American Institute of Physics, Melville, NY, US, Vol. 72, No. 2, January 12, 1998.					
EXAMINER CRANE				DATE CONSIDERED 6/2006			
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INFORMATION DISCLOSURE CITATION <i>(Use several sheets if necessary)</i>				ATTY DOCKET NO. F05-420-US		APPLICATION NO. 2004416 <i>Not Yet Assigned</i>			
				APPLICANT(S) Masanobu ANDO, et al.				19 JAN 2006 FILING DATE 2006.01.19 GROUP-ART UNIT Concurrently Herewith <i>Not Yet Assigned</i>	
				FILING DATE 2006.01.19					
U.S. PATENT DOCUMENTS									
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE		
<i>SWL</i>		6,100,586	08/08/2000	Chen et al.					
<i>SWL</i>		5,578,839	11/26/1996	Nakamura et al.					
U.S. PATENT APPLICATION PUBLICATIONS									
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE		
FOREIGN PATENT DOCUMENTS									
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO		
<i>SWL</i>		2002-43695	02/08/2002	Japan			ABS		
		2003-197969	07/11/2003	Japan			ABS		
		2003-101081	04/04/2003	Japan			ABS		
		11-46038	02/16/1999	Japan			ABS		
<i>SWL</i>		11-16812	01/22/1999	Japan			ABS		
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)									
<i>SWL</i>		R.P. Schneider, Jr. et al., "MOVPE growth of InAlGaP-based visible vertical-cavity surface-emitting lasers" Journal of Crystal Growth 124 (1992) 763-771 North-Holland							
<i>SWL</i>		S. Keller et al., "Growth of bulk InGaP films and quantum wells by atmospheric pressure metalorganic chemical vapour deposition" Journal of Crystal Growth 170 (1997) 349-352							
EXAMINER ORANG				DATE CONSIDERED 6/2006					
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INFORMATION DISCLOSURE CITATION <i>(Use several sheets if necessary)</i>				ATTY DOCKET NO. F05-420-US		APPLICATION NO. 10/554416	
				Masanobu IARBO Rec'd PCT/PTO 12 JAN 2006		No. of Claims Assigned 16	
				FILING Concurrently Herewith		GROUP ART Not Yet Assigned	

U.S. PATENT DOCUMENTS							
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FOREIGN PATENT DOCUMENTS								
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
SWC		2003-229645	08/15/2003	Japan			ABS	
		2002-16284	01/18/2002	Japan			ABS	
		2003-234545	08/22/2003	Japan			ABS	
SWC		2001-160627	06/12/2001	Japan			ABS	

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)			
SWC			C.F. Klingshirn, "Semiconductor Optics" Springer, p284-331

EXAMINER <div style="text-align: center; font-size: 1.2em;">CRANE</div>	DATE CONSIDERED <div style="text-align: center; font-size: 1.2em;">6/2006</div>
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